

L Number	Hits	Search Text	DB	Time stamp
-	2332	etch\$3 same (oxide sio2 "sio.sub.2" TEOS) same (nitride SiN Si3N4 "Si.sub.3 N.sub.4") AND ((polymer polymeric) same deposit\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 09:58
-	686	etch\$3 same (oxide sio2 "sio.sub.2" TEOS) same (nitride SiN Si3N4 "Si.sub.3 N.sub.4") same ((polymer polymeric) same deposit\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 09:59
-	36	etch\$3 same ((oxide sio2 "sio.sub.2" TEOS) with (nitride SiN Si3N4 "Si.sub.3 N.sub.4") with (underlying overlying)) same ((polymer polymeric) same deposit\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 10:59
-	20	(etch\$3 same ((oxide sio2 "sio.sub.2" TEOS) with (nitride SiN Si3N4 "Si.sub.3 N.sub.4") with (underlying overlying)) same ((polymer polymeric) same deposit\$3)) and high adj density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 10:02
-	0	((etch\$3 same ((oxide sio2 "sio.sub.2" TEOS) with (nitride SiN Si3N4 "Si.sub.3 N.sub.4") with (underlying overlying)) same ((polymer polymeric) same deposit\$3)) and high adj density) and ceiling with temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 10:02
-	0	((etch\$3 same ((oxide sio2 "sio.sub.2" TEOS) with (nitride SiN Si3N4 "Si.sub.3 N.sub.4") with (underlying overlying)) same ((polymer polymeric) same deposit\$3)) and high adj density) and ceiling with (heat\$3 cool\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 10:03
-	0	(etch\$3 same ((oxide sio2 "sio.sub.2" TEOS) with (nitride SiN Si3N4 "Si.sub.3 N.sub.4") with (underlying overlying)) same ((polymer polymeric) same deposit\$3)) and ceiling with (heat\$3 cool\$3 temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 10:03
-	5	(etch\$3 same (oxide sio2 "sio.sub.2" TEOS) same (nitride SiN Si3N4 "Si.sub.3 N.sub.4") same ((polymer polymeric) same deposit\$3)) and ceiling with (heat\$3 cool\$3 temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 10:04
-	26	(etch\$3 same (oxide sio2 "sio.sub.2" TEOS) same (nitride SiN Si3N4 "Si.sub.3 N.sub.4") AND ((polymer polymeric) same deposit\$3)) and ceiling with (heat\$3 cool\$3 temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 10:33
-	21	((etch\$3 same (oxide sio2 "sio.sub.2" TEOS) same (nitride SiN Si3N4 "Si.sub.3 N.sub.4") AND ((polymer polymeric) same deposit\$3)) and ceiling with (heat\$3 cool\$3 temperature)) not ((etch\$3 same (oxide sio2 "sio.sub.2" TEOS) same (nitride SiN Si3N4 "Si.sub.3 N.sub.4") same ((polymer polymeric) same deposit\$3)) and ceiling with (heat\$3 cool\$3 temperature))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 10:43
-	16	(etch\$3 same ((oxide sio2 "sio.sub.2" TEOS) with (nitride SiN Si3N4 "Si.sub.3 N.sub.4") with (underlying overlying)) same ((polymer polymeric) same deposit\$3)) not ((etch\$3 same ((oxide sio2 "sio.sub.2" TEOS) with (nitride SiN Si3N4 "Si.sub.3 N.sub.4") with (underlying overlying)) same ((polymer polymeric) same deposit\$3)) and high adj density)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 10:43

-	40	((etch\$3 same ((oxide sio2 "sio.sub.2" TEOS) with (nitride SiN Si3N4 "Si.sub.3 N.sub.4") with (underlying overlying)) same ((polymer polymeric) same deposit\$3)) ((etch\$3 same (oxide sio2 "sio.sub.2" TEOS) same (nitride SiN Si3N4 "Si.sub.3 N.sub.4") AND ((polymer polymeric) same deposit\$3)) and ceiling with (heat\$3 cool\$3 temperature))) and (CHF3 CF3H CH2F2 CF2H2 "CHF.sub.3" "CF.sub.3 H" "CH.sub.2 F.sub.2" "CF.sub.2 H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:01
-	9	(US-5801083-\$ or US-6180533-\$ or US-5477975-\$ or US-5722668-\$ or US-5865896-\$ or US-5990017-\$ or US-6296780-\$ or US-6465051-\$ or US-5399237-\$).did.	USPAT	2003/09/15 11:01
-	5	((((US-5801083-\$ or US-6180533-\$ or US-5477975-\$ or US-5722668-\$ or US-5865896-\$ or US-5990017-\$ or US-6296780-\$ or US-6465051-\$ or US-5399237-\$).did.)) and (CHF3 CF3H CH2F2 CF2H2 "CHF.sub.3" "CF.sub.3 H" "CH.sub.2 F.sub.2" "CF.sub.2 H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:02
-	5	(((((US-5801083-\$ or US-6180533-\$ or US-5477975-\$ or US-5722668-\$ or US-5865896-\$ or US-5990017-\$ or US-6296780-\$ or US-6465051-\$ or US-5399237-\$).did.)) and (CHF3 CF3H CH2F2 CF2H2 "CHF.sub.3" "CF.sub.3 H" "CH.sub.2 F.sub.2" "CF.sub.2 H.sub.2")) and (ar he H2 "h.sub.2" argon helium hydrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:04
-	5	(((((US-5801083-\$ or US-6180533-\$ or US-5477975-\$ or US-5722668-\$ or US-5865896-\$ or US-5990017-\$ or US-6296780-\$ or US-6465051-\$ or US-5399237-\$).did.)) and (CHF3 CF3H CH2F2 CF2H2 "CHF.sub.3" "CF.sub.3 H" "CH.sub.2 F.sub.2" "CF.sub.2 H.sub.2")) and (ar he H2 "h.sub.2" argon helium hydrogen)) and bias\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 11:04
-	17	US-4786359-\$.DID. OR US-0074456-\$.DID. OR US-5770099-\$.DID. OR US-5880036-\$.DID. OR US-5888414-\$.DID. OR US-5990017-\$.DID. OR US-6036877-\$.DID. US-5779849-\$.DID. OR US-5599396-\$.DID.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 13:49
-	11	US-6024826-\$.DID. OR US-6165311-\$.DID. OR US-5556501-\$.DID. OR US-5770099-\$.DID. OR US-5477975-\$.DID. OR US-6077384-\$.DID.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 13:50